AS-07
www.oxfordplasma.de/process/si_afm_k.htm

OXFORD INSTRUMENTS

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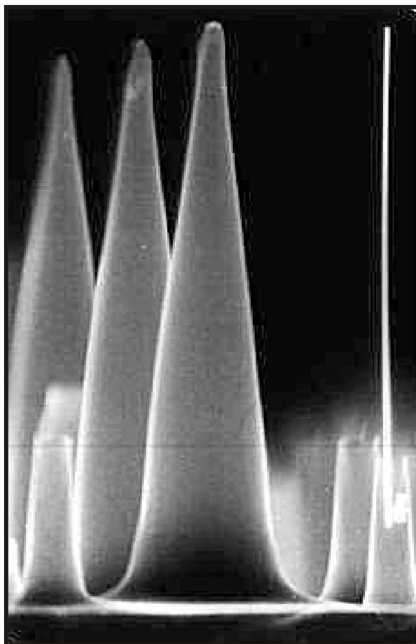
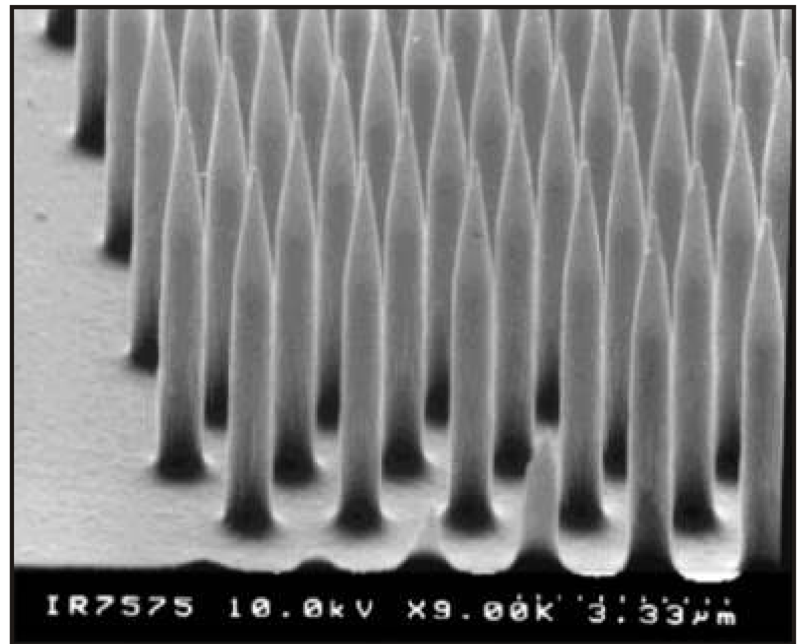
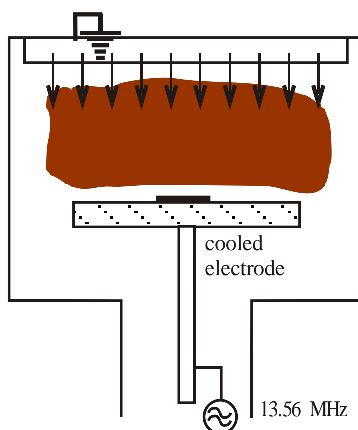
Plasmalab Data

Si Tips for AFM Microscopy





4 and 10 μm Peaks in Silicon
(Courtesy of University of Kassel, Institute of Technical Physics, Dr. I. Rangelow)



Technology:
Reactive Ion Etching (RIE)
13.56 MHz Plasma Excitation
Fluorine based Process

Results:
Rate : ca. 100nm / min
Mask: PR or SiO_2
Profile: controllable
two step process:
anisotropic/ isotropic

Plasmalab 80 Plus
Plasmalab 800 Plus
Plasmalab System 100
Plasmalab System 133